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# Shape anisotropy effects on magnetic domain wall dynamics in spintronic devices

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## Sponsors:

- Sandia National Laboratories
- O-REU at TAMU

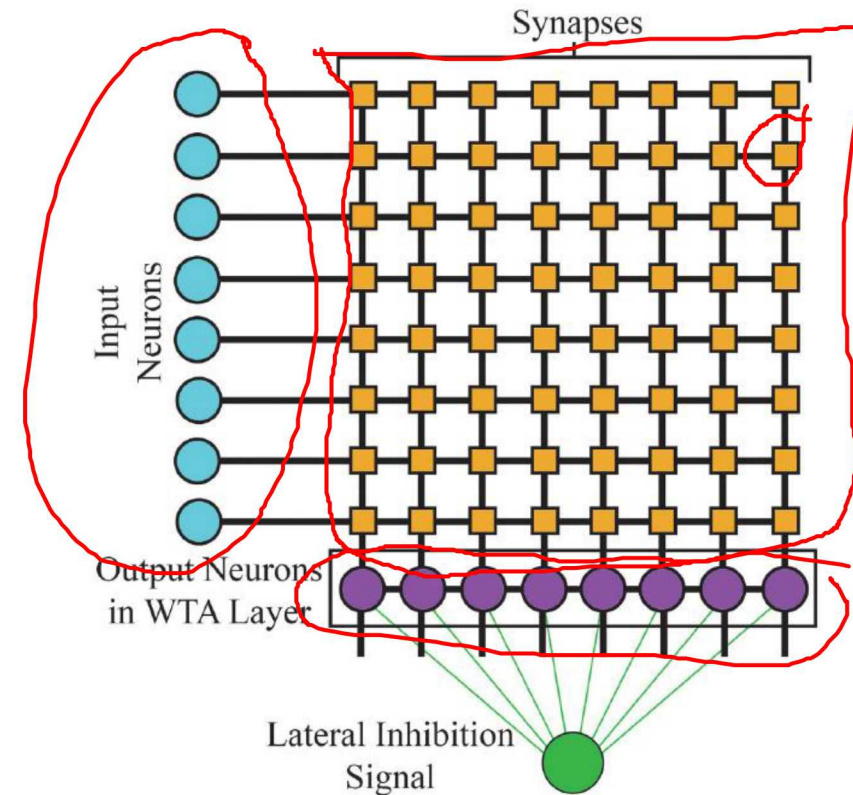
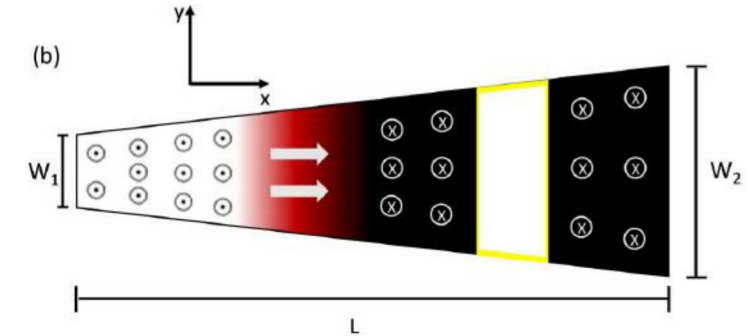
## Collaborators:

- Matthew Marinella
- Christopher Bennett
- Tianyao (Patrick) Xiao
- INC Lab at UT Austin

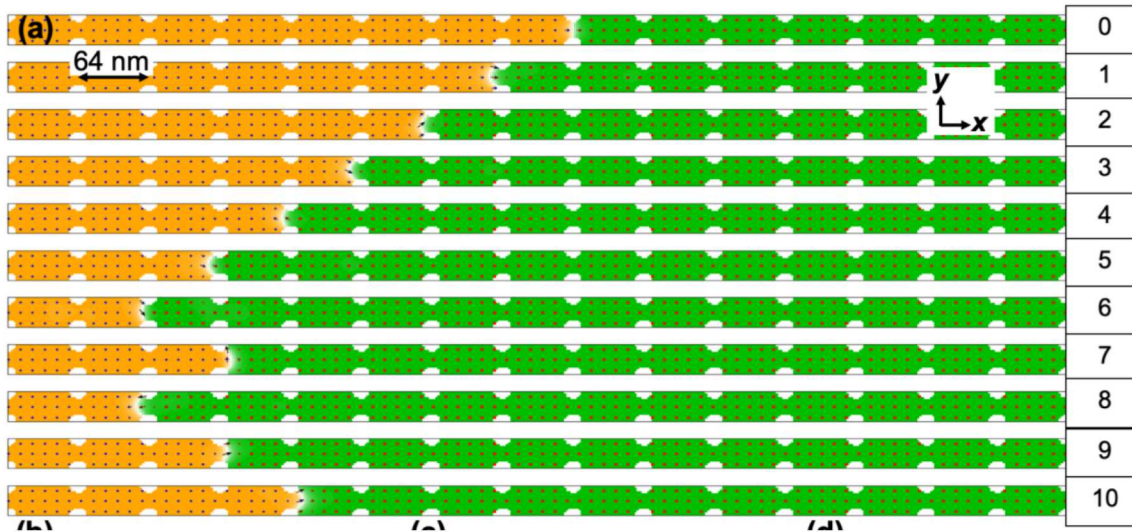


# Nanomagnetic Neural Networks

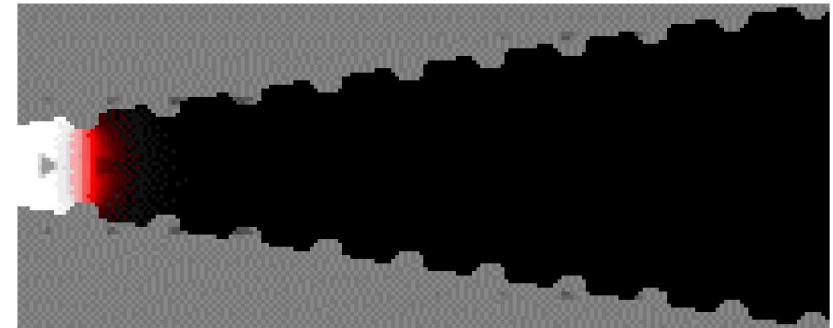
- Neural networks (NNs) are useful for pattern recognition tasks that humans are traditionally better at like speech and image recognition
- Synapses and neurons of a neural network can be implemented using spintronic domain wall devices
- Magnetic domain wall device current density vs synapse change linearity can be tuned to optimize NN training
- Goal: model shape-based nonlinear synaptic behavior at device and system level
  - Nonlinear synaptic behavior implement unsupervised learning



# Domain Wall Synapses



- Linear synapses implemented by rectangular channel
- Notches provide the fixed states/positions for the domain wall

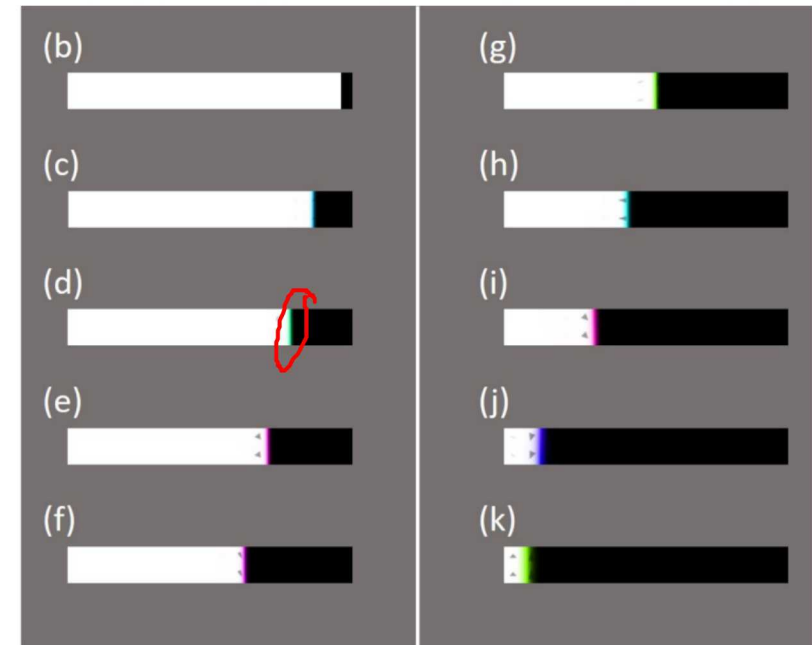


- Nonlinear tuning can be implemented by using sloped channel

# Micromagnetics and Analytical modeling

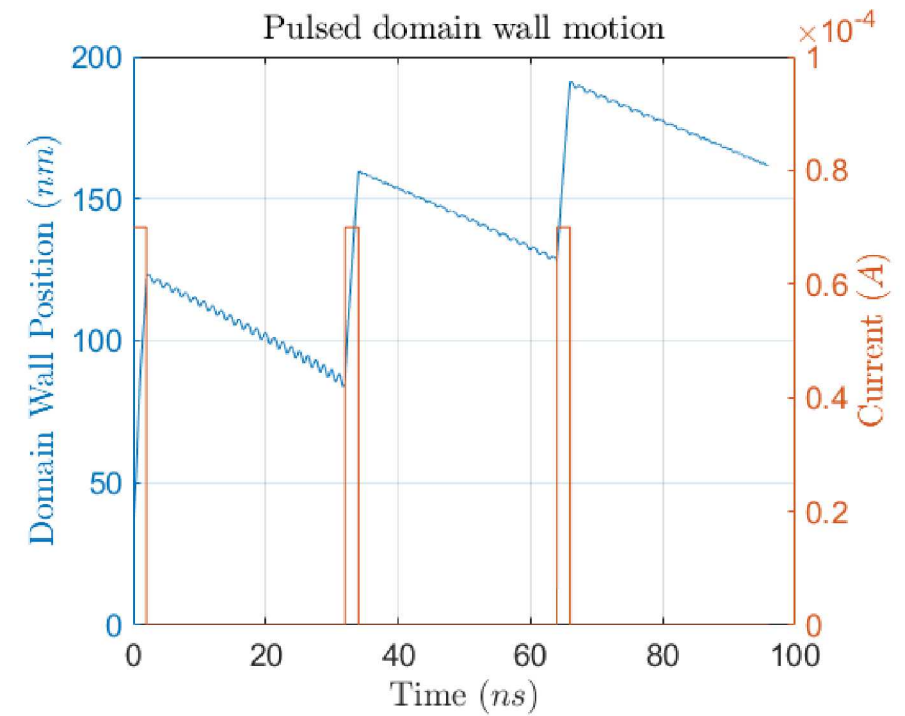
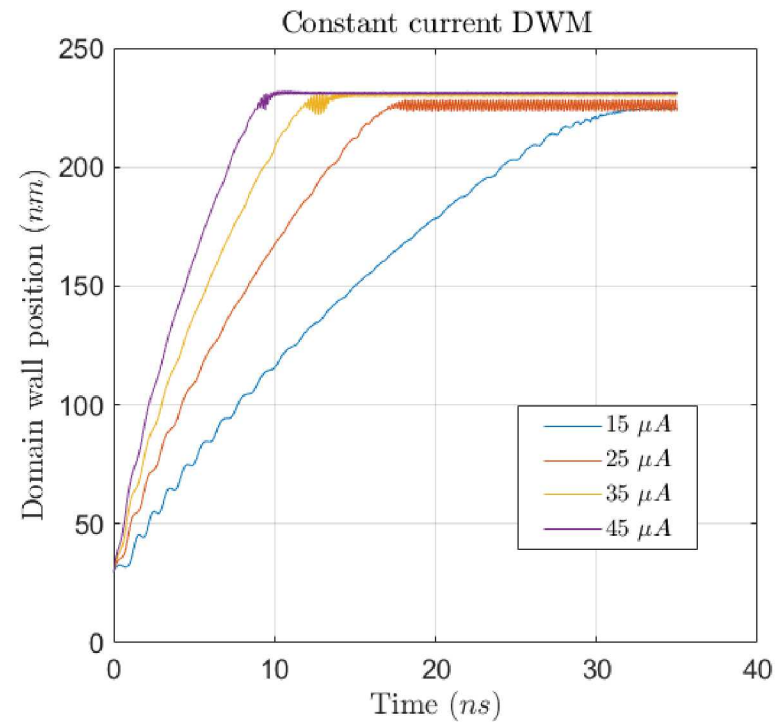
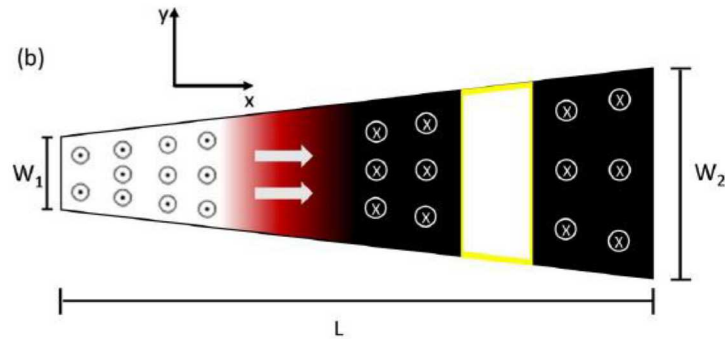
- Develop non-linear synapse model using micromagnetics simulation software MuMax3
- Produce SPICE compatible analytical device model
- Emphasis on ways to minimize leaking behavior in synapses

$$\vec{\tau}_{\text{ZL}} = \frac{1}{1 + \alpha^2} ((1 + \xi\alpha) \vec{m} \times (\vec{m} \times (\vec{u} \cdot \nabla) \vec{m}) + (\xi - \alpha) \vec{m} \times (\vec{u} \cdot \nabla) \vec{m})$$
$$\vec{u} = \frac{\mu_B \mu_0}{2e\gamma_0 B_{\text{sat}}(1 + \xi^2)} \vec{j}$$

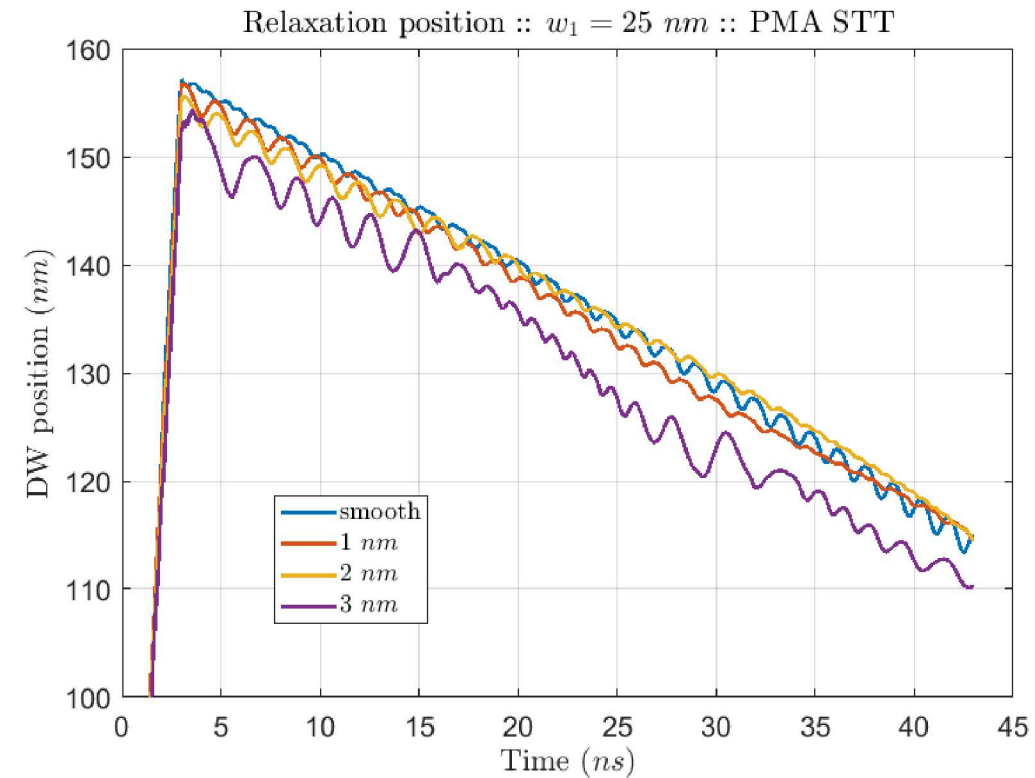
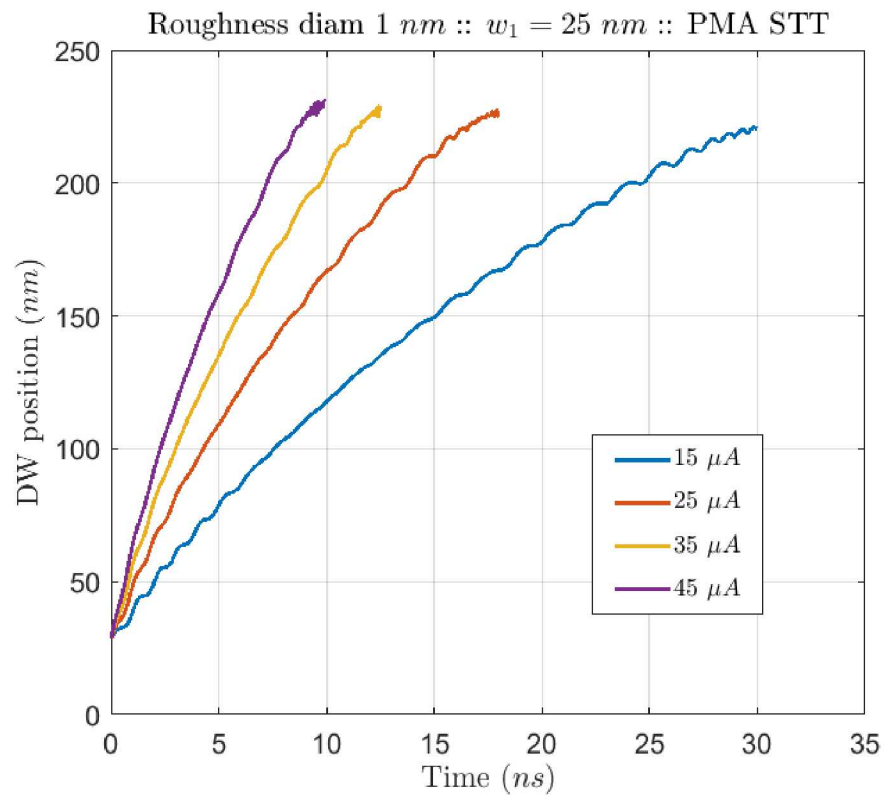




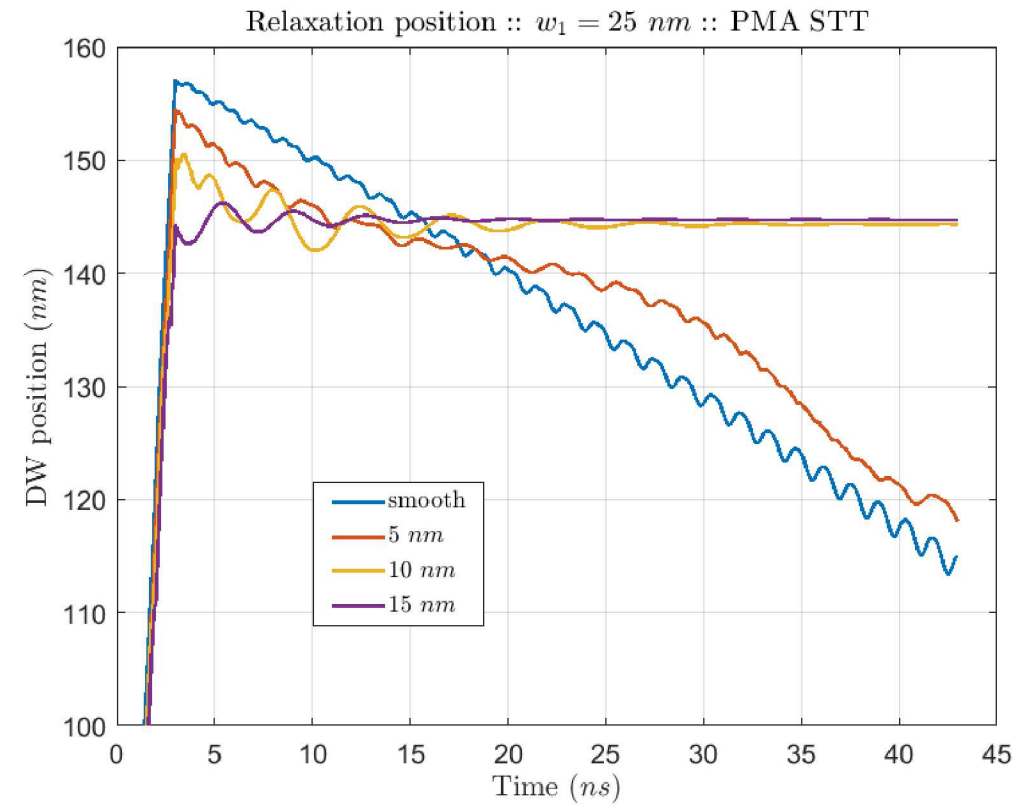
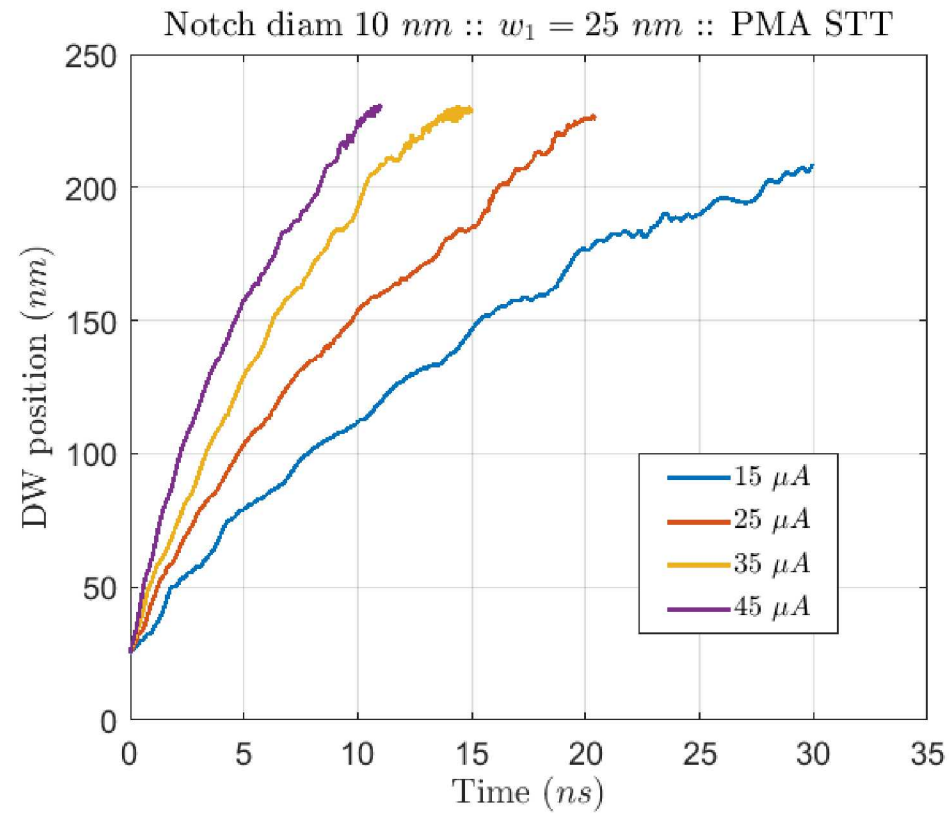
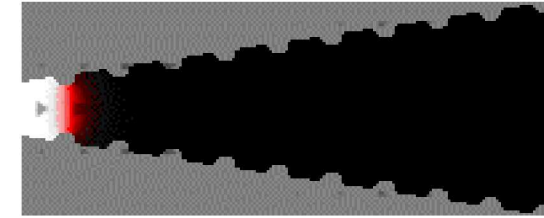
# Benchmark results for smooth synapse



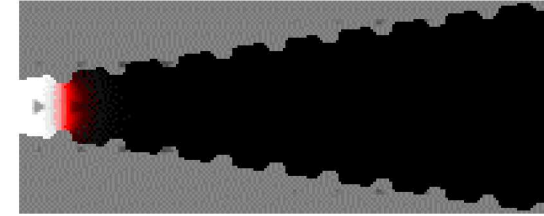
# Edge roughness does not impact synapse behavior



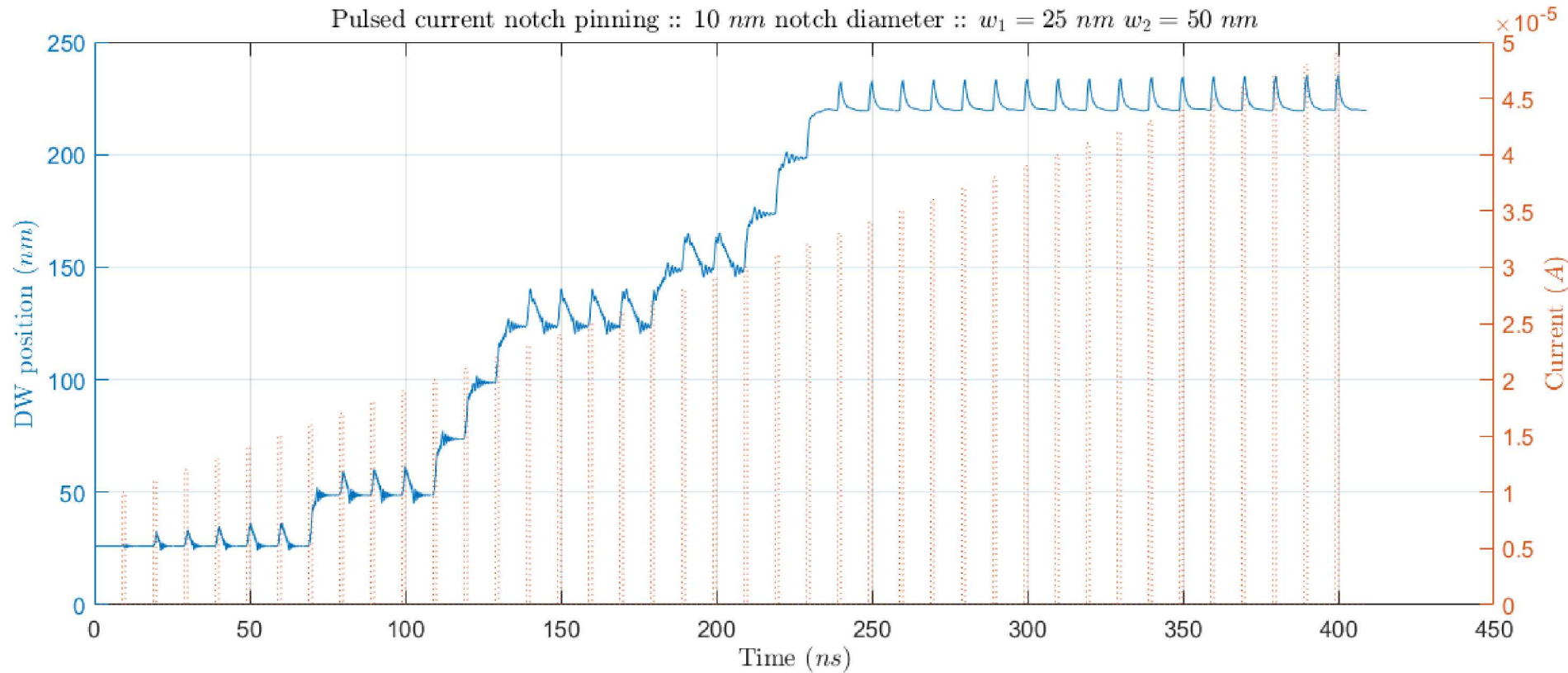
# Notches prevent leaking



# Notch pinning verification



Pulsed current notch pinning :: 10 nm notch diameter ::  $w_1 = 25$  nm  $w_2 = 50$  nm



## Observations:

- Pinning dependence likely dependent on Walker breakdown precession of domain wall
- Domain wall at wide end hard to pin, likely because of stronger edge effect



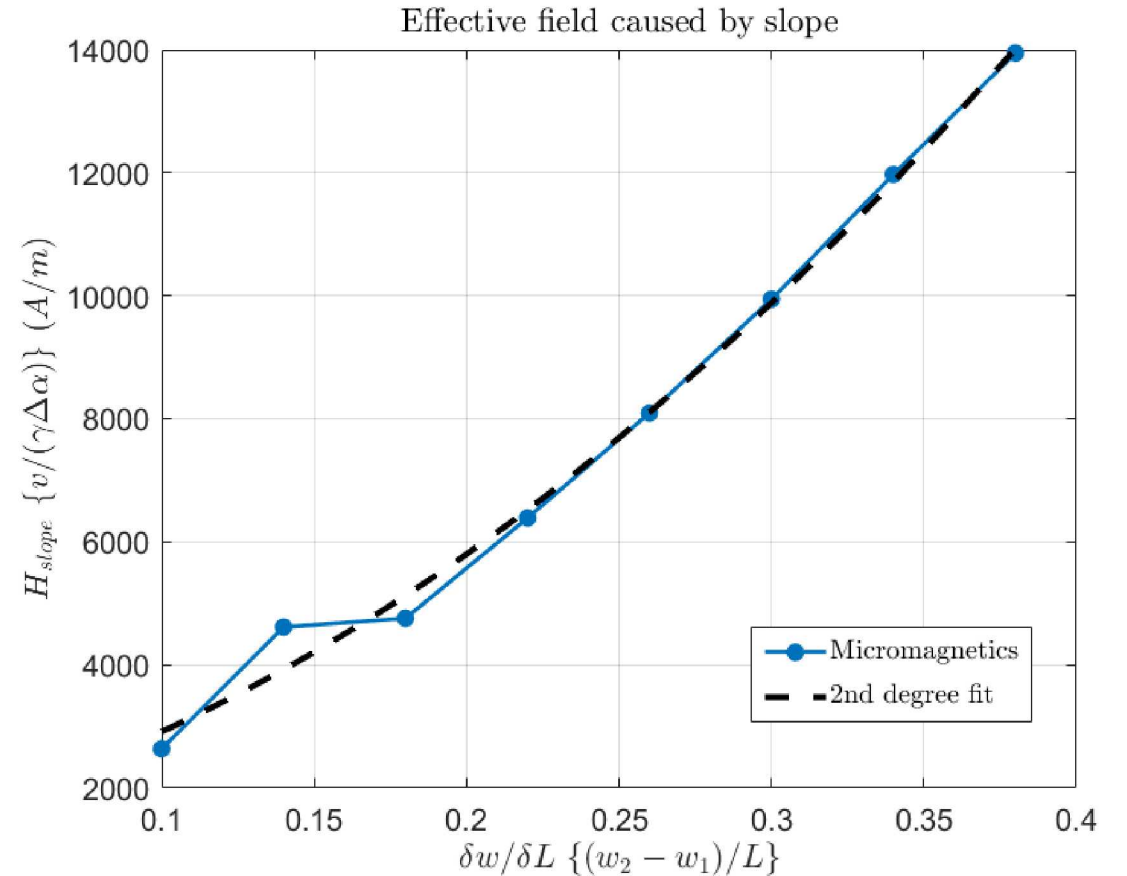
# Analytical modeling

- Approach: use 1D solution for DW motion in Walker breakdown regime
- Subsume all geometry based effects (slope, notches) into field term (H)

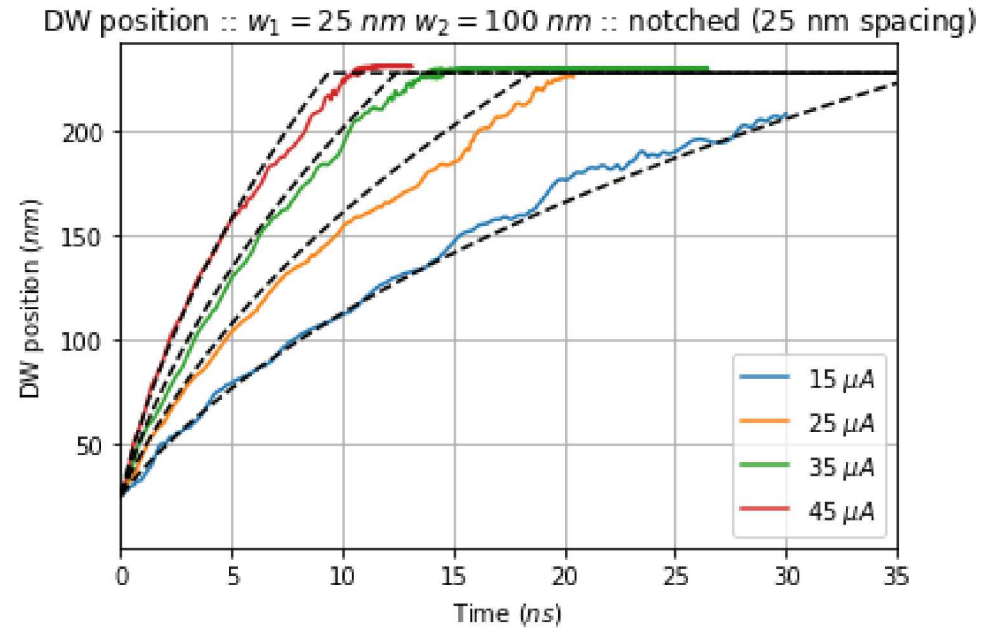
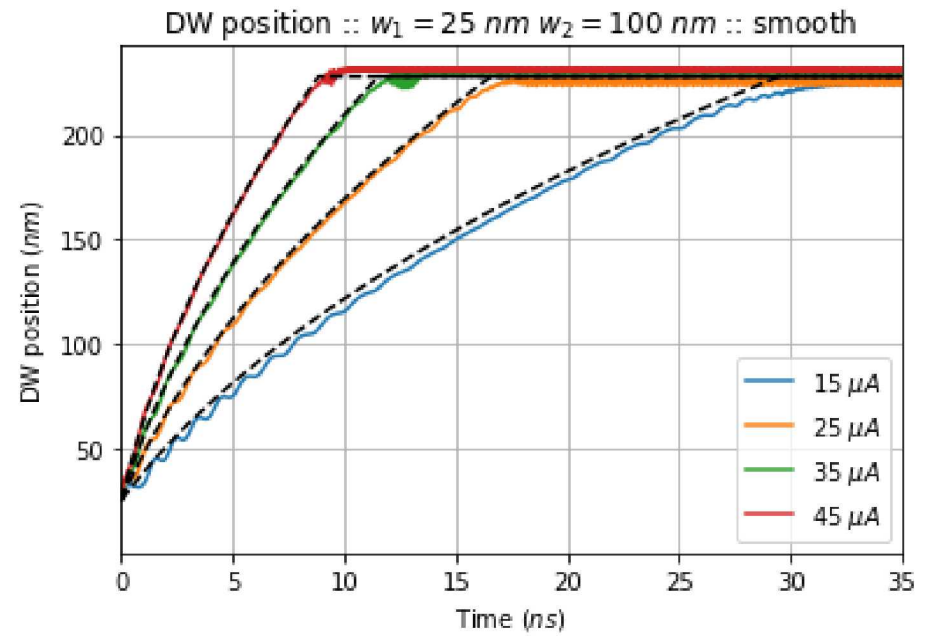
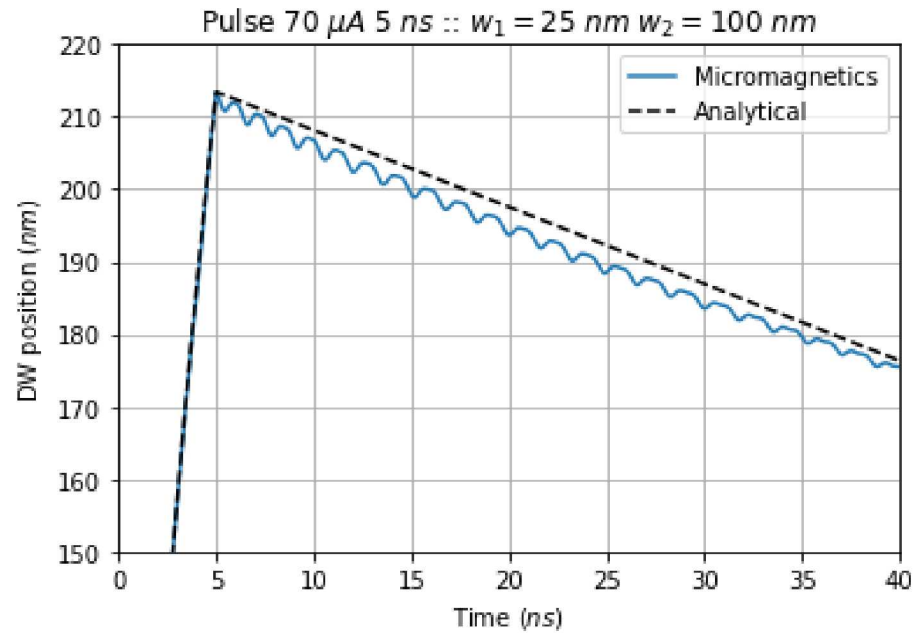
$$\bar{v} = \gamma \Delta \frac{\alpha}{1 + \alpha^2} \left( H + \frac{\beta u}{\gamma \Delta} \right) + \frac{u}{1 + \alpha^2}$$

$$u = \frac{g J_e \mu_B P}{2e M_s} \quad \beta = 0$$

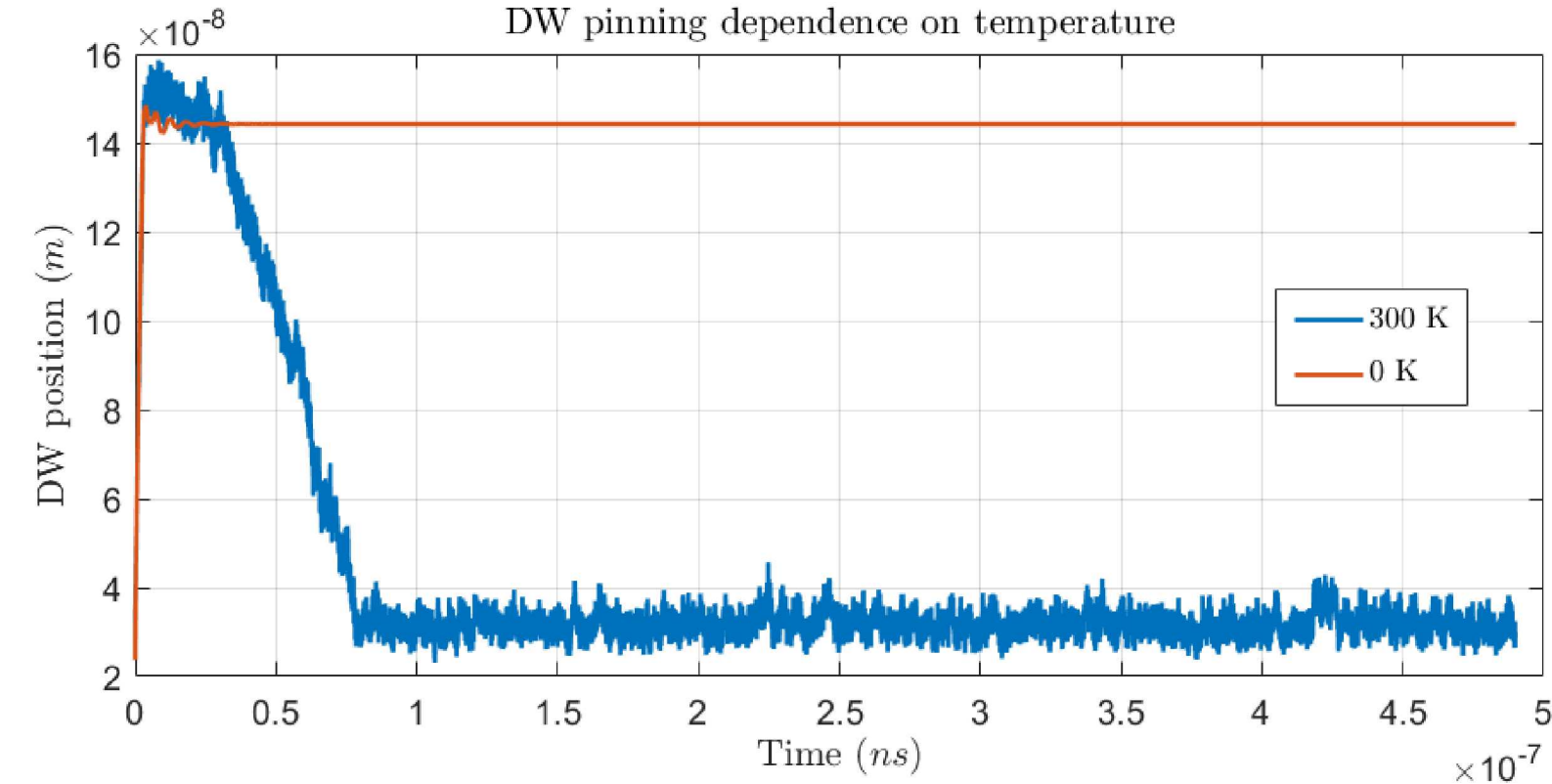
$$H = H_{slope} + H_{notch} + H_{demag}$$



# Analytical results



# Temperature Considerations



- Temperature causes noise, random motion for each spin in the system
- Random magnetization fluctuations due to heat cause gradual depinning
- Notches must provide energy well exceeding energy of heat fluctuation

# Conclusion

- Set up micromagnetics model of trapezoidal synapse using CoFeB material parameters with implementation of:
  - Spin transfer torque, spin Hall effect, Rashba effect
  - Notches and surface roughness
  - PMA vs IMA materials
- Notches were identified as a shape-related way to prevent leaking
- Analytical model useful for circuit-level simulations developed, with effects of geometry consumed into effective magnetic field term
- Limitations identified:
  - Resolution of device limited due to notches
  - Pinning effect dependent on temperature
  - Notches in different positions have different thresholds due to demagnetizing field

# Future Research

- Investigation into required notch depth to prevent depinning due to thermal fluctuations
- Improvement of notch field effects in analytical model
- Analyze multiple interacting devices and neural network update behavior